TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

GT80J101A

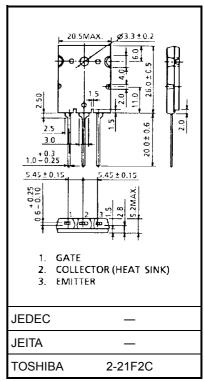
High Power Switching Applications

Unit: mm

- Enhancement-Mode
- High Speed: $t_f = 0.40 \mu s \text{ (max) (IC} = 80 \text{ A)}$
- Low Saturation Voltage: VCE (sat) = 3.0 V (max) (IC = 80 A)

Maximum Ratings (Ta = 25°C)

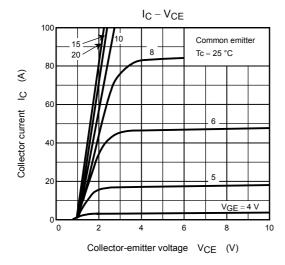
Characteristic	Symbol	Rating	Unit		
Collector-emitter voltage	V _{CES}	600	V		
Gate-emitter voltage		V _{GES}	±20	V	
Collector current	DC	Ic	80	Α	
	1ms	I _{CP}	160		
Collector power dissipation (Tc = 25°C)		PC	200	W	
Junction temperature		Tj	150	°C	
Storage temperature		T _{stg}	-55~150	°C	
Screw torque		_	0.8	N⋅m	

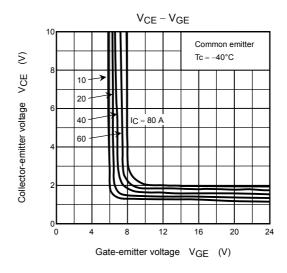


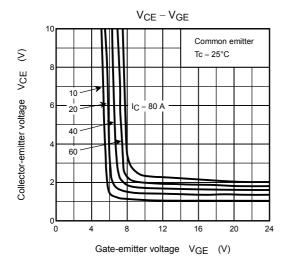
Weight: 9.75 g (typ.)

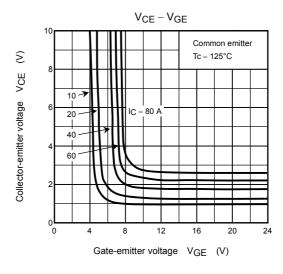
Electrical Characteristics (Ta = 25°C)

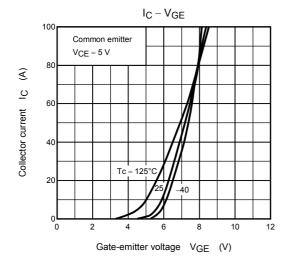
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage current		I _{GES}	$V_{GE} = \pm 25 \text{ V}, V_{CE} = 0$	_	_	±500	nA	
Collector cut-off current		I _{CES}	V _{CE} = 600 V, V _{GE} = 0	_	_	1.0	mA	
Gate-emitter cut-off voltage		V _{GE} (OFF)	V _{CE} = 5 V, I _C = 80 mA	3.0	_	6.0	V	
Collector-emitter saturation voltage		V _{CE} (sat) (1)	I _C = 10 A, V _{GE} = 15 V	_	_	2.0	V	
		V _{CE (sat)} (2)	$I_C = 80 \text{ A}, V_{GE} = 15 \text{ V}$	_	2.4	3.0	v	
Input capacitance		C _{ies}	$V_{CE} = 10 \text{ V}, V_{GE} = 0, f = 1 \text{ MHz}$	_	5500		pF	
Switching time	Rise time	t _r	$ \begin{array}{c c} 33 \Omega \\ V_{\text{IN}} & & & & & \\ \hline 15 V & & & & \\ \hline -15 V & & & & \\ \end{array} $ $ \begin{array}{c c} V_{\text{OUT}} \\ V_{\text{CC}} & & & \\ \hline \end{array} $	_	0.3	0.6	- μs	
	Turn-on time	t _{on}		_	0.5	0.8		
	Fall time	t _f		_	0.25	0.40		
	Turn-off time	t _{off}		_	0.7	1.0		
Thermal resistance		R _{th (j-c)}	_	_	_	0.625	°C/W	

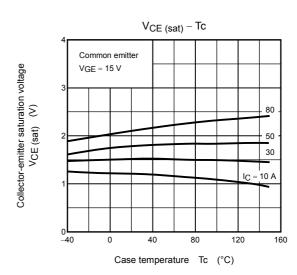


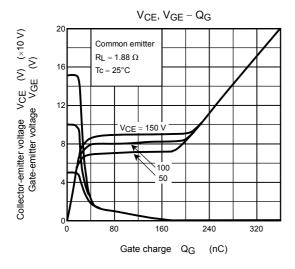


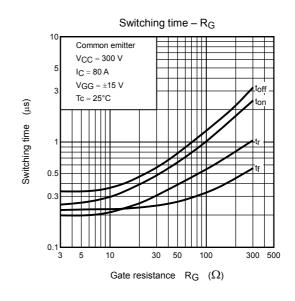


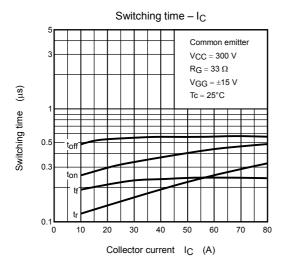


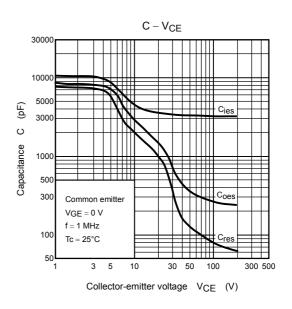


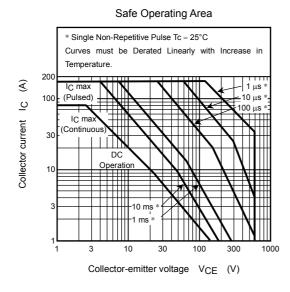


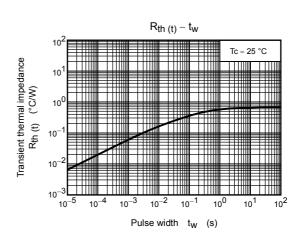




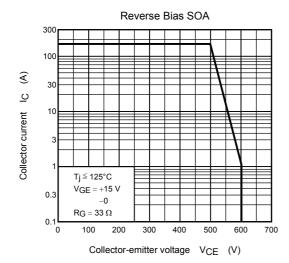








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